2SB0942 (2SB942), 2SB0942A (2SB942A)

Silicon PNP epitaxial planar type

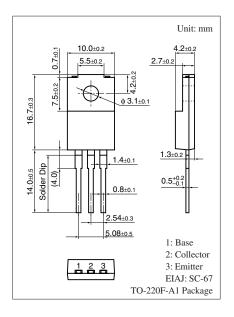
For low-frequency power amplification Complementary to 2SD1267, 2SD1267A

■ Features

- \bullet High forward current transfer ratio $h_{F\!E}$ which has satisfactory linearity
- Large collector-emitter saturation voltage V_{CE(sat)}
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage	2SB0942	V_{CBO}	-60	V
(Emitter open)	2SB0942A		-80	
Collector-emitter voltage	2SB0942	V _{CEO}	-60	V
(Base open)	2SB0942A		-80	
Emitter-base voltage (Coll	V_{EBO}	-5	V	
Collector current	I_C	-4	A	
Peak collector current	I_{CP}	-8	A	
Collector power	P _C	40	W	
dissipation	$T_a = 25^{\circ}C$		2	
Junction temperature	T _j	150	°C	
Storage temperature	T_{stg}	-55 to +150	°C	



■ Electrical Characteristics $T_C = 25$ °C ± 3 °C

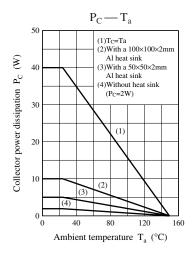
Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage	2SB0942	V _{CEO}	$I_C = -30 \text{ mA}, I_B = 0$	-60			V
(Base open)	2SB0942A			-80			
Base-emitter voltage		V_{BE}	$V_{CE} = -4 \text{ V}, I_{C} = -3 \text{ A}$			-2	V
Collector-emitter	2SB0942	I _{CES}	$V_{CE} = -60 \text{ V}, V_{BE} = 0$			-400	μΑ
cutoff current (E-B short)	2SB0942A		$V_{CE} = -80 \text{ V}, V_{BE} = 0$			-400	
Collector-emitter cutoff current (Base open)		I_{CEO}	$V_{CE} = -30 \text{ V}, I_B = 0$			-700	μΑ
Emitter-base cutoff current (Collector open)		I_{EBO}	$V_{EB} = -5 \text{ V}, I_C = 0$			-1	mA
Forward current transfer ratio		h _{FE1} *	$V_{CE} = -4 \text{ V}, I_{C} = -1 \text{ A}$	40		250	_
		h _{FE2}	$V_{CE} = -4 \text{ V}, I_{C} = -3 \text{ A}$	15			
Collector-emitter saturation voltage		V _{CE(sat)}	$I_C = -4 \text{ A}, I_B = -0.4 \text{ A}$			-1.5	V
Transition frequency		f_T	$V_{CE} = -10 \text{ V}, I_{C} = -0.1 \text{ A}, f = 10 \text{ MHz}$		30		MHz
Turn-on time		t _{on}	$I_C = -4 A, I_{B1} = -0.4 A, I_{B2} = 0.4 A$		0.2		μs
Storage time		t _{stg}	$V_{CC} = -50 \text{ V}$		0.5		μs
Fall time		t_{f}			0.2		μs

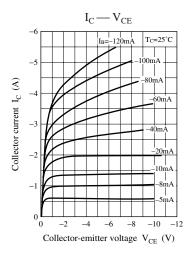
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

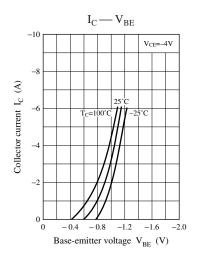
2. *: Rank classification

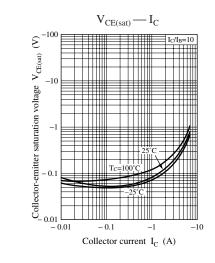
Rank	R	Q	Р
$h_{\rm FE1}$	40 to 90	70 to 150	120 to 250

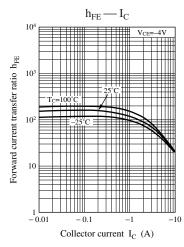
Note) The part numbers in the parenthesis show conventional part number.

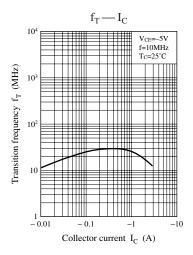


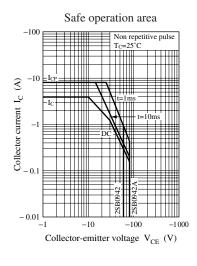


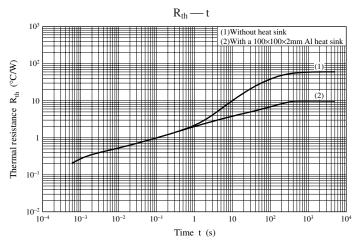












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